



### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
30V	34mΩ@10V	3.5A
	52mΩ@4.5V	

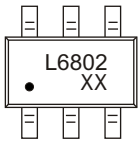
### Feature

- High power and current handing capability
- Surface mount package

### Application

- Battery protection
- Load switch
- Power management

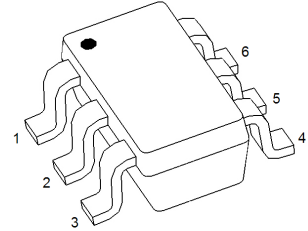
### MARKING:



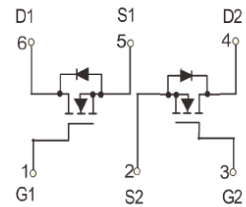
L6802 = Device Code

XX = Date Code

### SOT-23-6L



### Schematic diagram



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1,2</sup>	$I_D$	3.5	A
Pulsed Drain Current	$I_{DM}$	14	A
Power Dissipation	$P_D$	1.9	W
Thermal Resistance from Junction to Ambient <sup>1</sup>	$R_{\theta JA}$	65	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

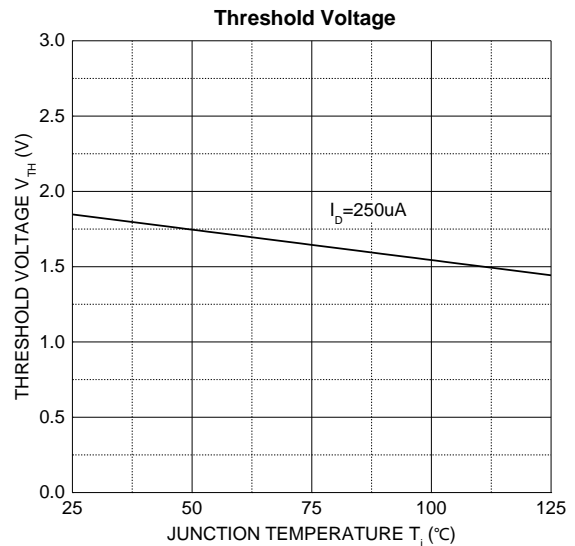
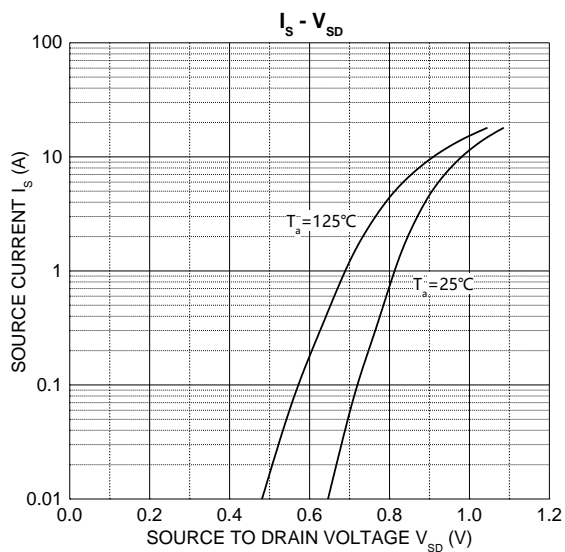
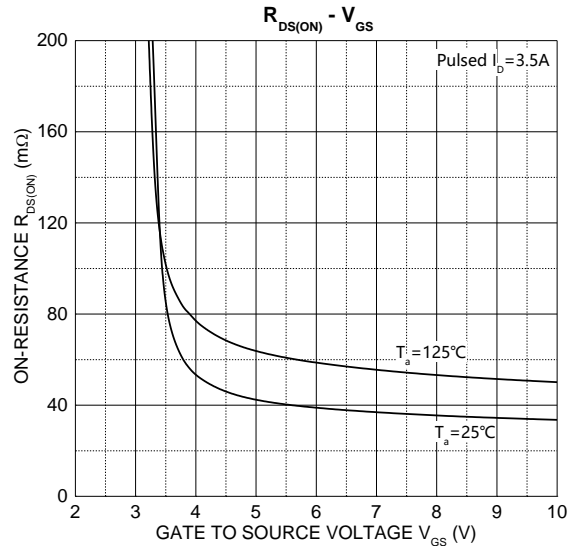
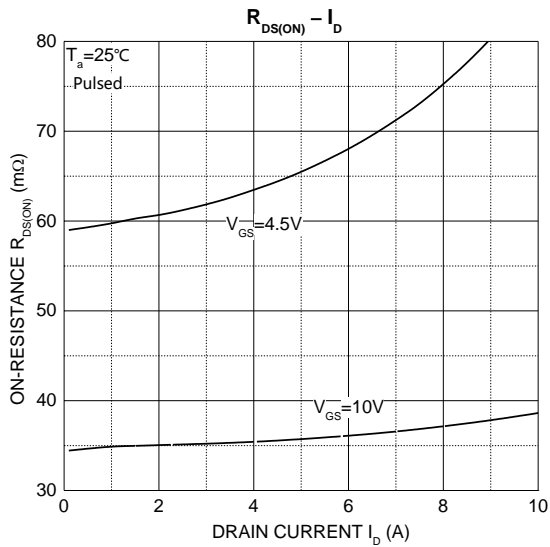
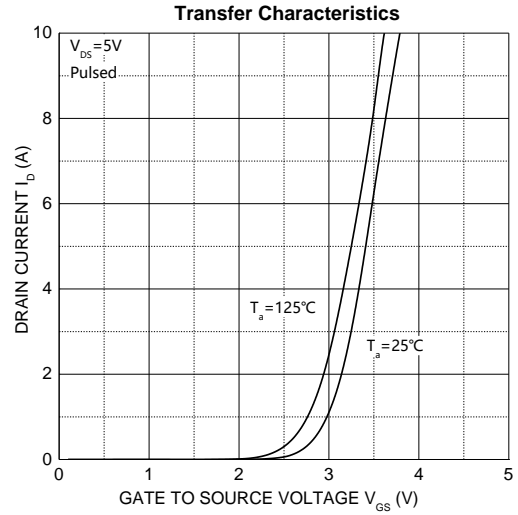
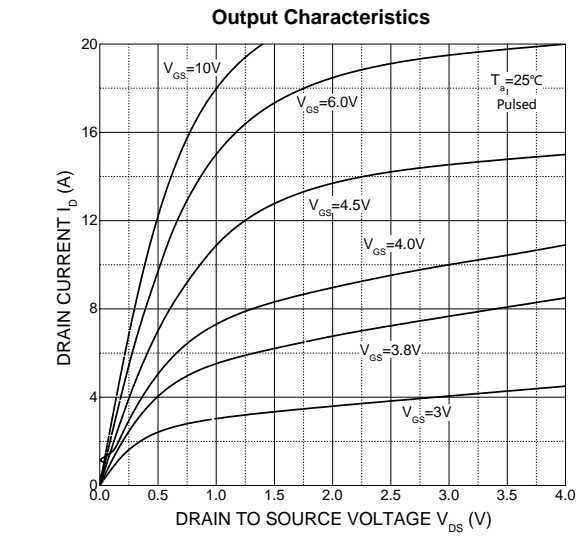
**MOSFET ELECTRICAL CHARACTERISTICS(T<sub>A</sub> = 25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V			1	μA
Gate - body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
<b>On Characteristics<sup>3</sup></b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1	1.8	3	V
Drainsource Onresistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.5A		34	45	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2A		52	70	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 3.5A		4		S
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz		227		pF
Output Capacitance	C <sub>oss</sub>			46		
Reverse Transfer Capacitance	C <sub>rss</sub>			38		
<b>Switching Characteristics</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15V, I <sub>D</sub> = 3.5A, V <sub>GS</sub> = 10V		4.5		nC
Gate-source Charge	Q <sub>gs</sub>			0.95		
Gate-drain Charge	Q <sub>gd</sub>			0.75		
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = 15V, R <sub>L</sub> = 4.2Ω, V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 3Ω		5		ns
Turn-on Rise Time	t <sub>r</sub>			2		
Turn-off Delay Time	t <sub>d(off)</sub>			21		
Turn-off Fall Time	t <sub>f</sub>			18		
<b>Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 3.5A			1.2	V

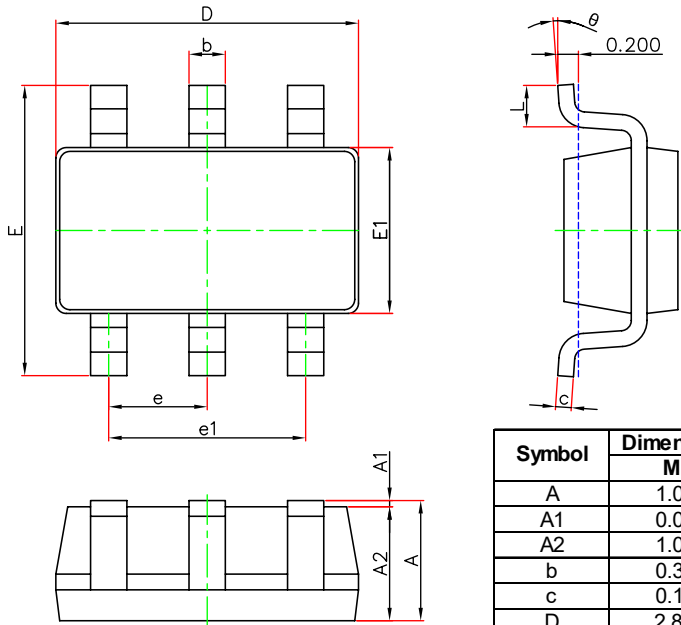
Notes :

- 1.R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR4 board with 1oz. single side copper, in a still air environment with T<sub>A</sub> = 25°C.
- 2.R<sub>θJA</sub> is measured in the steady state
- 3.Pulse test : Pulse width ≤ 380μs, duty cycle ≤ 2%.

**Typical Characteristics**



## SOT-23-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°